Ordering Information

Part Number	Package	Packing
HV857K7-G	8-Lead DFN	3000/Reel
HV857MG-G	8-Lead MSOP	2500/Reel

⁻G denotes a lead (Pb)-free / RoHS compliant package

Absolute Maximum Ratings

Parameter	Value
Supply voltage, V _{DD}	-0.5V to 6.5V
Operating temperature	-40°C to +85°C
Storage temperature	-65°C to +150°C
DFN-8 power dissipation	1.6W
MSOP-8 power dissipation	300mW
Output voltage, V _{cs}	-0.5 to +120V

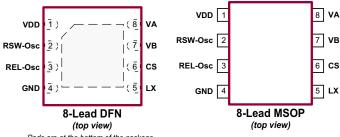
Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Typical Thermal Resistance

Package	$oldsymbol{ heta}_{ja}$
8-Lead DFN	37°C/W
8-Lead MSOP	171°C/W

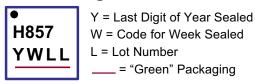
Mounted on FR4 board, 25mm x 25mm x 1.57mm

Pin Configuration



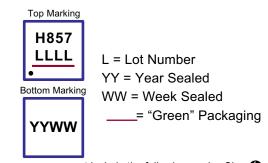
Pads are at the bottom of the package. Exposed center pad is at ground potential.

Product Marking



Package may or may not include the following marks: Si or 🚯

8-Lead DFN



Package may or may not include the following marks: Si or

8-Lead MSOP

Recommended Operating Conditions

Sym	Parameter	Min	Тур	Max	Units	Conditions
V _{DD}	Supply voltage	1.8	-	5.0	V	
f _{EL}	Operating drive frequency	_	-	1.0	kHz	
T _A	Operating temperature	-40	-	+85	οС	

Enable/Disable Function Table

Sym	Parameter	Min	Тур	Max	Units	Conditions
EN-L	Logic input low voltage	0	-	0.2	V	$V_{DD} = 1.8 \text{ to } 5.0 \text{V}$
EN-H	Logic input high voltage	V _{DD} - 0.2	-	V _{DD}	V	$V_{DD} = 1.8 \text{ to } 5.0 \text{V}$

DC Electrical Characteristics (Over recommended operating conditions unless otherwise specified, T_a = 25°C)

Sym	Parameter	Min	Тур	Max	Units	Conditions
R _{DS(ON)}	On-resistance of switching transistor	-	-	6.0	Ω	I = 100mA
V _{cs}	Max. output regulation voltage	85	95	105	V	V _{DD} =1.8 to 5.0V

DC Electrical Characteristics (cont.)

Sym	Parameter	Min	Тур	Max	Units	Conditions
$V_A - V_B$	Peak to Peak output voltage	170	190	210	V	V _{DD} =1.8 to 5.0V
l _{DDQ}	Quiescent V _{DD} supply current	-	-	150	nA	R _{SW-Osc} = Low
I _{DD}	Input current going into the VDD pin	-	-	150	μA	V _{DD} = 1.8 to 5.0V. See Figure 1
I _{IN}	Input current including inductor current	-	20	25	mA	See Figure 1*
V _{cs}	Output voltage on VCS	-	84	-	V	See Figure 1
f _{EL}	EL lamp frequency	205	240	275	Hz	See Figure 1
f _{sw}	Switching transistor frequency	-	80	-	kHz	See Figure 1
D	Switching transistor duty cycle	-	88	-	%	See Figure 1

^{*} The inductor used is a 220μH Murata inductor, max DC resistance of 8.4Ω, part # LQH32CN221K21.

Block Diagram

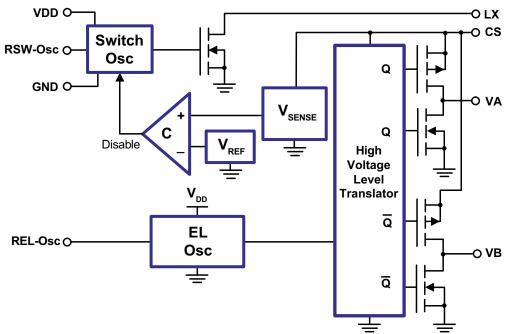
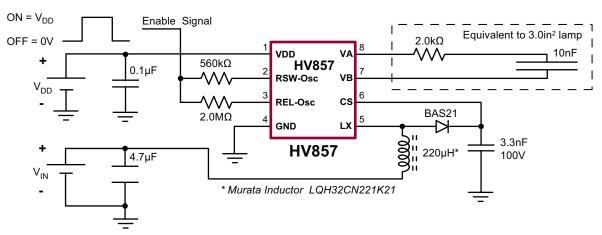


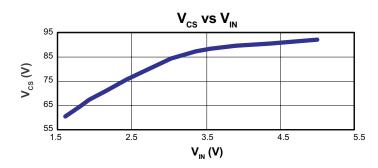
Figure 1: Typical Application/ Test Circuit

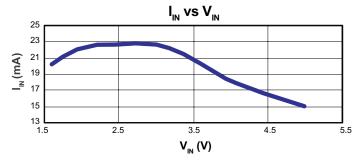


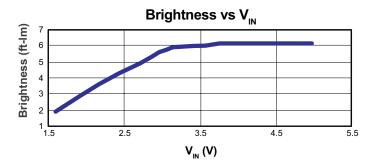
Typical Performance

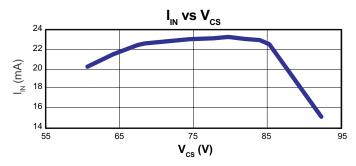
Device	Lamp Size	$V_{DD} = V_{IN}$	I _{IN}	V _{cs}	$\mathbf{f}_{\scriptscriptstyle{EL}}$	Brightness	
HV857MG-G	3.0in ²	3.3V	20.0mA	84V	240Hz	6.0ft-Im	

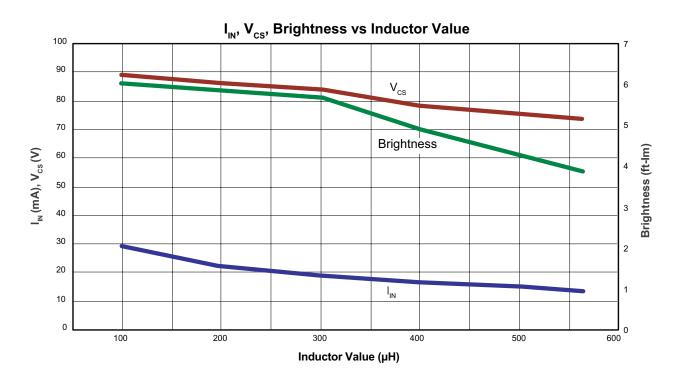
Typical Performance Curves for Figure 1 (EL Lamp = 3.0in², V_{DD} = 3.0V)











External Component Description

External Component	Description
Diode	Fast reverse recovery diode, BAS21 diode or equivalent.
C _s Capacitor	0.003μF to 0.1μF, 100V capacitor to GND is used to store the energy transferred from the inductor.
R _{EL} Resistor	The EL lamp frequency is controlled via an external $R_{\rm EL}$ resistor connected between REL-Osc and VDD of the device. The lamp frequency increases as $R_{\rm EL}$ decreases. As the EL lamp frequency increases, the amount of current drawn from the battery will increase and the output voltage $V_{\rm CS}$ will decrease. The color of the EL lamp is dependent upon its frequency. A 2M Ω resistor would provide lamp frequency of 205 to 275Hz. Decreasing the $R_{\rm EL}$ resistor by a factor of 2 will increase the lamp frequency by a factor of 2. $f_{\rm EL} = \frac{(2M\Omega)(240{\rm Hz})}{R_{\rm EL}}$
R _{sw} Resistor	The switching frequency of the converter is controlled via an external resistor, RSW between RSW-Osc and VDD of the device. The switching frequency increases as $R_{\rm SW}$ decreases. With a given inductor, as the switching frequency increases, the amount of current drawn from the battery will decrease and the output voltage, $V_{\rm CS}$, will also decrease. $f_{\rm SW} = \frac{(560k\Omega)(80Hz)}{R_{\rm SW}}$
L _x Inductor	The inductor L_{χ} is used to boost the low input voltage by inductive flyback. When the internal switch is on, the inductor is being charged. When the internal switch is off, the charge stored in the inductor will be transferred to the high voltage capacitor C_{s} . The energy stored in the capacitor is connected to the internal H-bridge, and therefore to the EL lamp. In general, smaller value inductors, which can handle more current, are more suitable to drive larger size lamps. As the inductor value decreases, the switching frequency of the inductor (controlled by R_{sw}) should be increased to avoid saturation. A 220 μ H Murata (LQH32CN221) inductor with 8.4 Ω series DC resistance is typically recommended. For inductors with the same inductance value, but with lower series DC resistance, lower R_{sw} resistor value is needed to account high surrent draw and inductor actuation.
Lamp	is needed to prevent high current draw and inductor saturation. As the EL lamp size increases, more current will be drawn from the battery to maintain high voltage across the EL lamp. The input power, $(V_{IN} \times I_{IN})$, will also increase. If the input power is greater than the power dissipation of the package, an external resistor in series with one side of the lamp is recom-
	mended to help reduce the package power dissipation.



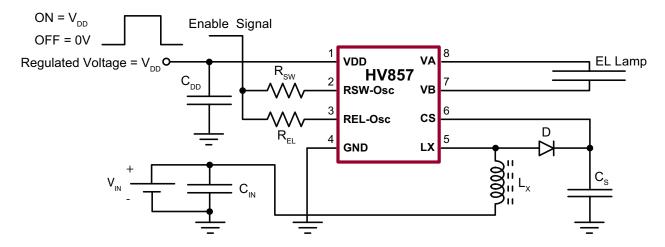
Split Supply Configuration

The HV857 can also be used for handheld devices operating from a battery where a regulated voltage is available. This is shown in Figure 2. The regulated voltage can be used to run the internal logic of the HV857. The amount of current necessary to run the internal logic is 150 μ A Max at a V_{DD} of 3.0V. Therefore, the regulated voltage could easily provide the current without being loaded down.

Enable/Disable Configuration

The HV857 can be easily enabled and disabled via a logic control signal on the $R_{\rm SW}$ and $R_{\rm EL}$ resistors as shown in Figure 2 below. The control signal can be from a microprocessor. The control signal has to track the $V_{\rm DD}$ supply. $R_{\rm SW}$ and $R_{\rm EL}$ are typically very high values. Therefore, only 10's of microamperes will be drawn from the logic signal when it is at a logic high (enable) state. When the microprocessor signal is high the device is enabled, and when the signal is low, it is disabled.

Figure 2: Split Supply and Enable/Disable Configuration

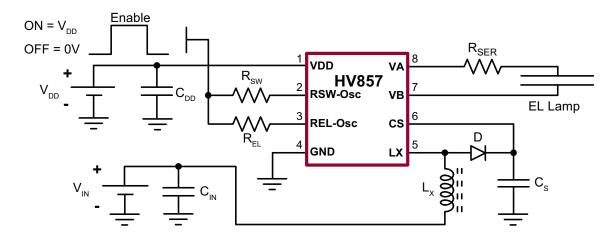


Audible Noise Reduction

This section describes a method (patented) developed at Supertex to reduce the audible noise emitted by the EL lamps used in application sensitive to audible noise. Figure

3 shows a general circuit schematic that uses the resistor, $\mathbf{R}_{\text{SER}},$ connected in series with the EL lamp.

Figure 3: Typical Application Circuit for Audible Noise Reduction



Minimization of EL Lamp Audible Noise

The EL lamp, when lit, emits an audible noise. This is due to EL lamp construction and it creates a major problem for applications where the EL lamp can be close to the ear such as cellular phones. The noisiest waveform is a square wave and the quietest waveform has been assumed to be a sine wave.

After extensive research, Supertex has developed a waveform that is quieter than a sine wave. The waveform takes the shape of approximately 2RC time constants for rising and 2RC time constants for falling, where C is the capacitance of the EL lamp, and R is the external resistor, R_{SER} , connected in series with the EL lamp. This waveform has been proven to generate less noise than a sine wave.

The audible noise from the EL lamp can be set at a desired level based on the series resistor value used with the lamp. It is important to note that use of this resistor will reduce the voltage across the lamp. Reduction of voltage across the lamp will also have another effect on the over all performance of the Supertex EL drivers, age compensation (patented). This addresses a very important issue, EL lamp life that most mobile phone manufacturers are concerned about.

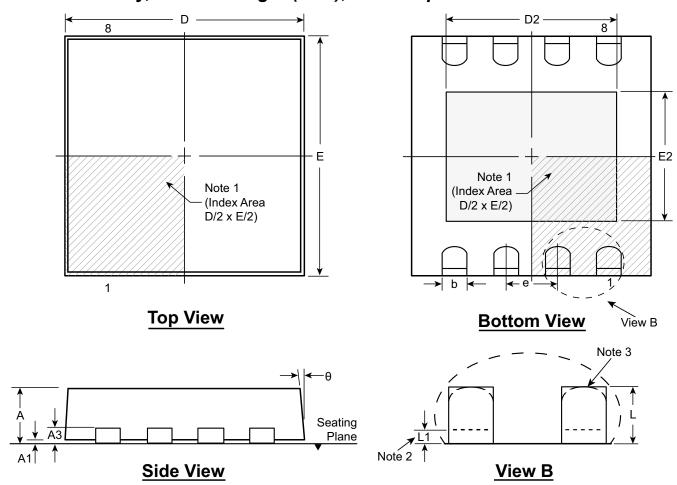
Effect of Series Resistor on EL Lamp Audible Noise and Brightness

As EL lamp ages, its brightness is reduced and its capacitance is diminished. By using the RC model to reduce the audible noise emitted by the EL lamp, the voltage across the lamp will increase as its capacitance diminishes. Hence the increase in voltage will compensate for the reduction of the brightness. As a result, it will extend the EL lamp's half-life (half the original brightness).

Increasing the value of the series resistor with the lamp will reduce the EL lamp audible noise as well as its brightness. This is due to the fact that the output voltage across the lamp will be reduced and the output waveform will have rounder edges.

8-Lead DFN Package Outline (K7)

3.00x3.00mm body, 0.80mm height (max), 0.65mm pitch



Notes:

- A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.
- 2. Depending on the method of manufacturing, a maximum of 0.15mm pullback (L1) may be present.
- 3. The inner tip of the lead may be either rounded or square.

Symbo	ol	Α	A1	А3	b	D	D2	E	E2	е	L	L1	θ
Dimension (mm)	MIN	0.70	0.00		0.25	2.85*	1.60	2.85*	1.35	0.65 BSC	0.30	0.00*	0o
	NOM	0.75	0.02	0.20 REF	0.30	3.00	-	3.00	-		0.40	-	-
	MAX	0.80	0.05		0.35	3.15*	2.50	3.15*	1.75		0.50	0.15	14°

JEDEC Registration MO-229, Variation WEEC-2, Issue C, Aug. 2003.

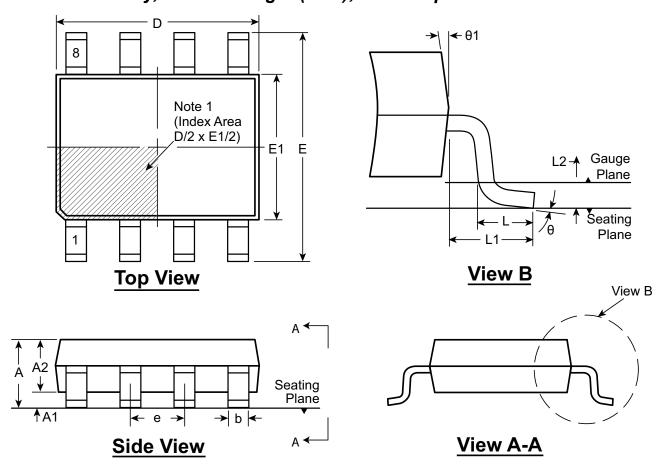
Drawings not to scale.

Supertex Doc. #: DSPD-8DFNK73X3P065, Version C081109.

^{*} This dimension is not specified in the JEDEC drawing.

8-Lead MSOP Package Outline (MG)

3.00x3.00mm body, 1.10mm height (max), 0.65mm pitch



Note:

1. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.

Symbo	ol	Α	A1	A2	b	D	E	E1	е	L	L1	L2	θ	θ1
	MIN	0.75*	0.00	0.75	0.22	2.80*	4.65*	2.80*		0.40			0 °	5°
Dimension (mm)	NOM	-	-	0.85	-	3.00	4.90	3.00	0.65 BSC	0.60	0.95 REF	0.25 BSC	-	-
()	MAX	1.10	0.15	0.95	0.38	3.20*	5.15*	3.20*		0.80			8 º	15°

JEDEC Registration MO-187, Variation AA, Issue E, Dec. 2004.

Drawings are not to scale.

Supertex Doc. #: DSPD-8MSOPMG, Version H041309.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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^{*} This dimension is not specified in the JEDEC drawing.